Supporting information for:

Photolithographic Patterning of Alkoxy Substituted Poly(*p*-phenylenevinylene)s from Xanthate Precursors

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Received (in XXX, XXX) Xth XXXXXXXX 20XX, Accepted Xth XXXXXXXX 20XX DOI: 10.1039/b000000x



Fig. S1 Variable temperature UV-Vis (A) and TGA (B) of precursor DM-PPV **3.** (Temperatures above 220 °C caused a hypochromic and hypochromic shift of the UV-Vis λ_{max}).



Fig. S2 Variable temperature UV-Vis (A) and TGA (B) of precursor MH-PPV 7. (Temperatures above 220 °C caused a hypochromic and hypochromic shift of the UV-Vis λ_{max}).



Fig. S3 UV-Vis of xanthate precursor DM-PPV **3** with no PAG, with a 15 sec (463 mJ cm⁻²) exposure, with 5% PAG-1 and a 15 sec exposure, and with no PAG and a 30 sec (919 mJ cm⁻²) exposure. The 30 sec exposure shows the lowest intensity xanthate band and the highest intensity oligomeric band indicating a greater degree of xanthate elimination. However, a 30 sec exposure does not provide a solubility change sufficient such that the patterned area can be developed.



Fig. S4 Optical images of xanthate precursor DM-PPV **3**, patterned using 4- (phenylthiophenyl)diphenylsulfonium triflate). The same conditions described in the main text were utilized, except the exposure times were slightly reduced (10 sec, 313 mJ/cm² for large features sizes (mm), 3 sec, 101 mJ/cm² for small feature sizes (μ m)).